30A 650V Trench Field stop IGBT with anti-parallel diode SRE30N065FSU2DF

General Description

The SRE30N065FSU2DF is a Field Stop Trench IGBT with anti-parallel diode, which offers ultra-low switching losses, high energy efficiency for switching applications such as PFC, Power Supply, Inverter, etc.

The SRE30N065FSU2DF is available in TO-247、TO-263 and TO-220C packages.

Features

- High Breakdown Voltage to 650V
- Advanced Trench Fieldstop technology
  - Ultra low E_{off}
  - High Ruggedness, Temperature Stability
  - Easy Parallel Switching Capability due to Positive Temperature Coefficient in $V_{CE(SAT)}$
- Enhanced Avalanche Capability
- Non-Automotive Qualified

Application

- Inverter
- Uninterruptible power supplies
- PFC application
- Converter with high switching frequency

Symbol

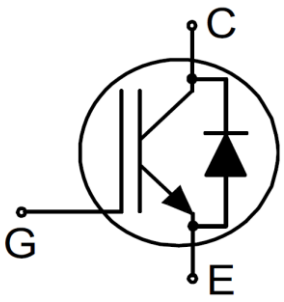
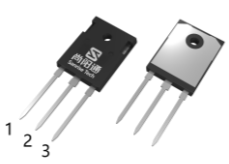
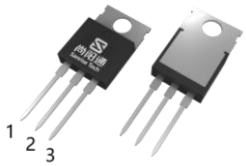


Figure 1 Symbol of SRE30N065FSU2DF

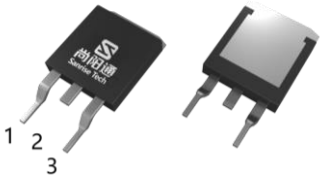
Package Type



TO-247



TO-220C



TO-263

Pin 1- Gate
Pin 2&backside- Collector
Pin 3-Emitter

Figure 2 Package Type of SRE30N065FSU2DF

Ordering Information

SRE30N065FSU2DF□□–□

Circuit Type
Package
S2: TO-263; T: TO-247; TC:TO-220C

G: Green
Blank: Tube
TR: Tape & Reel

Package	Part Number	Marking ID	Packing Type
TO-263	SRE30N065FSU2DFS2TR-G2	SR30N065FSU2DFS2G2	Tape & Reel
TO-247	SRE30N065FSU2DFT-G2	SRE30N065FSU2DFTG2	Tube
TO-220C	SRE30N065FSU2DFTC-G2	SRE30N065FSU2DFTCG2	Tube

30A 650V Trench Field stop IGBT with anti-parallel diode SRE30N065FSU2DF

Absolute Maximum Ratings

Parameter		Symbol	Rating	Unit
Collector-emitter Voltage		V_{CES}	650	V
Gate-emitter Voltage		V_{GES}	±20	V
Transient Gate-emitter Voltage			±30	V
Continuous Collector Current	T_C=25ºC	I_C	55	A
	T_C=100ºC		30	
Pulsed Collector Current, Limited by T_{Jmax}		I_{CM}	90	A
Diode Continuous Collector Current	T_C=25ºC	I_F	50(1)	A
	T_C=100ºC		30	
Diode Pulsed Current, Limited by T_{Jmax}		I_{FM}	90	A
Power Dissipation	T_C=25ºC	P_{tot}	170	W
	T_C=100ºC		85	
Short Circuit withstand time: V_{GE}=15V,Vcc≤400V,Tj_start=25℃; Allow number of short circuits<1000; Time between short circuits:1.0S;		tsc	6	us
Operating Junction Temperature Range		T_J	-40 ~ 175(2)	ºC
Storage Temperature Range		T_{STG}	-55 ~ 150	ºC
Lead Temperature (Soldering, 10 sec)		T_{LEAD}	260	ºC

Note:
1. Current level is limited by Tj_max.
2. Reliability testing conducted at Tj=175℃.

Thermal Resistance

Parameter	Symbol	Min.	Typ.	Max.	Unit
IGBT Thermal Resistance，Junction-to-Case	R_{thJC}	-	-	0.88	ºC/W
Diode Thermal Resistance，Junction-to-Case	R_{thJC}	-	-	1.6	
Thermal Resistance，Junction-to-Ambient	R_{thJA}	-	-	40	

30A 650V Trench Field stop IGBT with anti-parallel diode SRE30N065FSU2DF

Electrical Characteristics

T_J = 25ºC, unless otherwise specified.

Parameter		Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Statistic Characteristics							
Collector-emitter Breakdown Voltage		BV_{CES}	V_{GE}=0V, I_C=250μA	650			V
Gate Threshold Voltage		$V_{GE(th)}$	V_{CE}=V_{GE}, I_C=250μA	3.8	4.32	5.1	V
Collector-emitter saturation voltage		V_{CEsat}	V_{GE}=15V, I_C=30A, T_J=25ºC		1.52	2.0	V
			T_J=125ºC		1.8		V
			T_J=175ºC		1.96		V
Zero Gate Voltage Collector Current		I_{CES}	V_{CE}=650V, V_{GE}=0V T_J=25ºC		0.1	40	μA
			T_J=175ºC			1	mA
Gate-emitter Leakage Current	Forward	I_{GESF}	V_{GE}=20V, V_{CE}=0V			100	nA
	Reverse	I_{GESR}	V_{GE}=-20V, V_{CE}=0V			-100	nA
Dynamic Characteristics							
Input Capacitance		C_{IES}	V_{CE}=25V, V_{GE}=0V, f=1 MHz		1678		pF
Output Capacitance		C_{OES}			144		
Reverse Transfer Capacitance		C_{RES}			29		
Gate Resistance		R_G	f=1 MHz, Open Drain		1.1		Ω
Turn-on Delay Time		$t_{d(on)}$	T_J=25ºC V_{CC}=400V, I_C=30A R_G=10Ω, V_{GE}=0/15V Energy losses include "tail" and diode reverse recovery		13		ns
Rise Time		t_r			14		ns
Turn-off Delay Time		$t_{d(off)}$			100		ns
Fall Time		t_f			72		ns
Turn-on energy		E_{on}			0.78		mJ
Turn-off energy		E_{off}			0.38		mJ
Total switching energy		E_{ts}			1.16		mJ
Turn-on Delay Time		$t_{d(on)}$	T_J=150ºC V_{CC}=400V, I_C=30A R_G=10Ω,V_{GE}=0/15V Energy losses include "tail" and diode reverse recovery		13		ns
Rise Time		t_r			16		ns
Turn-off Delay Time		$t_{d(off)}$			131		ns
Fall Time		t_f			130		ns
Turn-on energy		E_{on}			0.97		mJ
Turn-off energy		E_{off}			0.7		mJ
Total switching energy		E_{ts}			1.67		mJ
Gate to Emitter Charge		Q_{GE}	V_{CC}=400V, I_C=30A V_{GE}=0 to 15V		12		nC
Gate to Collector Charge		Q_{GC}			37		
Gate Charge Total		Q_G			67		

30A 650V Trench Field stop IGBT with anti-parallel diode SRE30N065FSU2DF

Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Reverse Diode Characteristics						
Diode Forward Voltage	V_F	I_F=15A T_J=25ºC		1.44	1.9	V
		I_F=15A T_J=125ºC		1.25		
		I_F=15A T_J=175ºC		1.19		
		I_F=30A T_J=25ºC		1.75	2.1	V
		I_F=30A T_J=125ºC		1.64		
		I_F=30A T_J=175ºC		1.61		
Reverse Recovery Time	t_{rr}	T_J=25ºC V_R=400V, I_F=30A dI_F/dt=570A/μs		150		ns
Reverse Recovery Charge	Q_{rr}			630		nC
Peak Reverse Recovery Current	I_{rrm}			17		A

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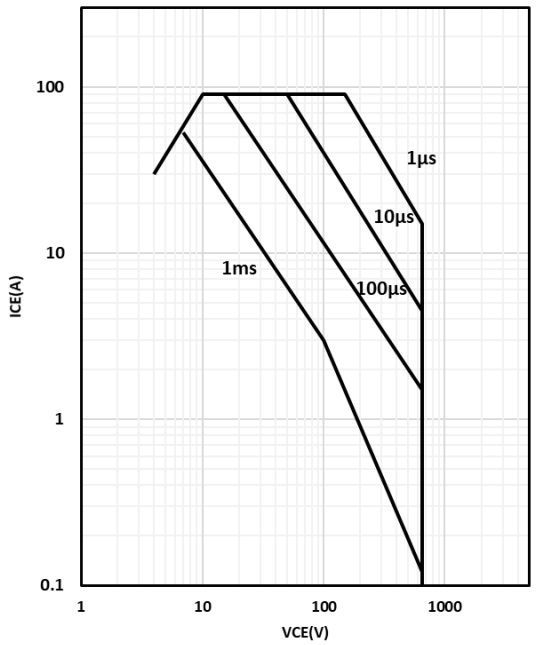
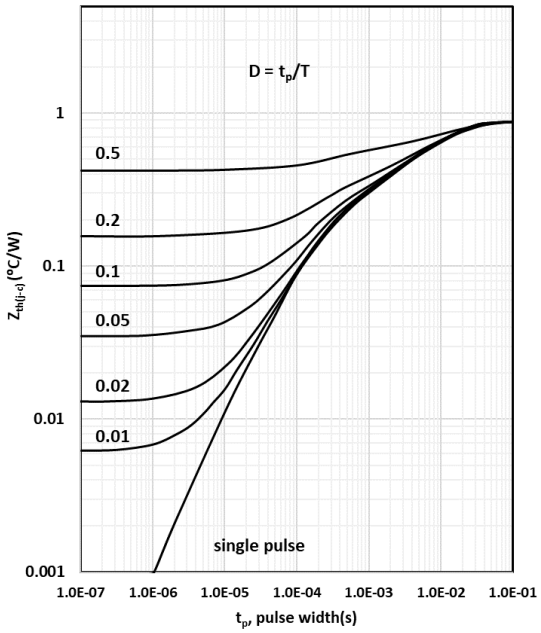
Typical Performance Characteristics

Figure 3: IGBT FBSOA



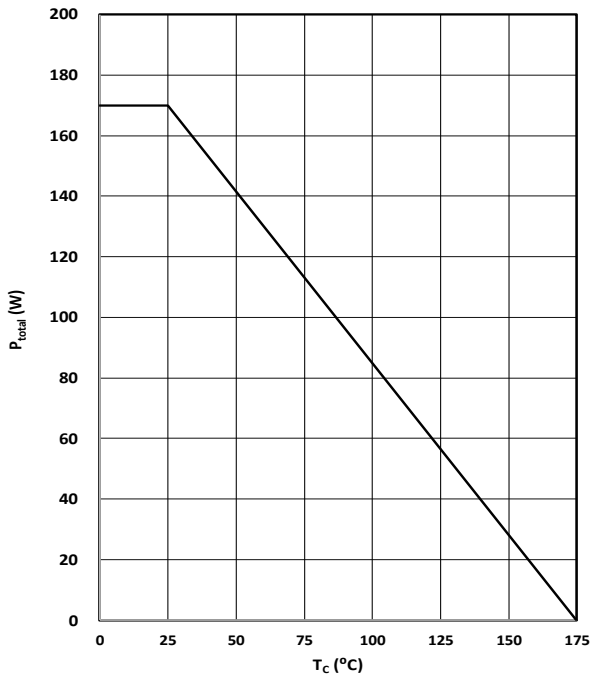
$I_C = f(V_{CE})$; $V_{GE} \geq 15/0V$; $Tj \leq 175^oC$

Figure 4: IGBT transient thermal impedance



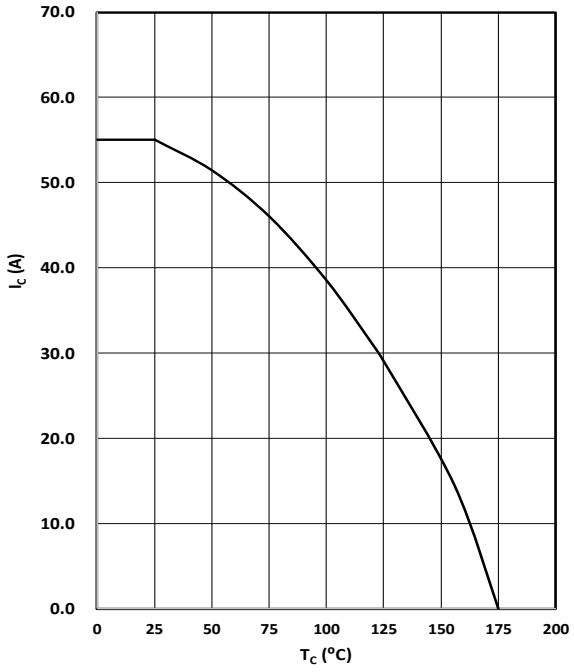
$R_{th(J-C)} = f(t_p)$; duty cycle: $D = t_p/T$

Figure 5: Power dissipation



Ptot= f(Tc);

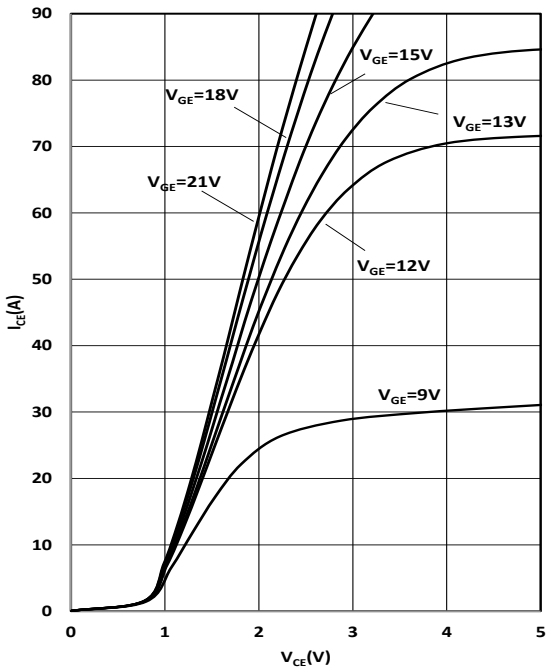
Figure 6: Collector current vs. temperature



Ic= f(Tj); $V_{GE} \geq 15V$; $Tj \leq 175^oC$

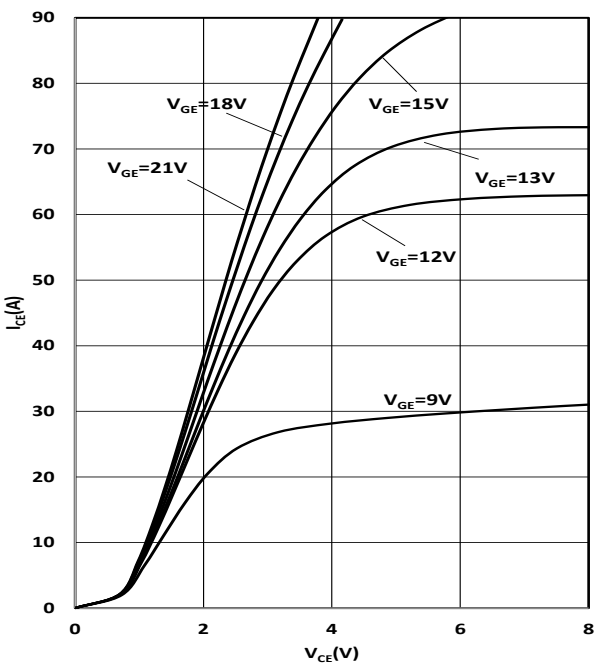
30A 650V Trench Field stop IGBT with anti-parallel diode SRE30N065FSU2DF

Figure 7: Typical Output Characteristics



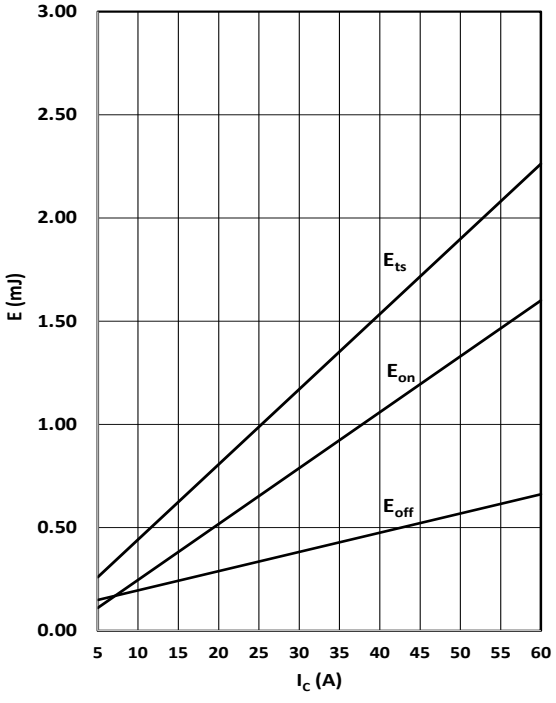
$I_C = f(V_{CE})$; Tj= 25ºC; parameter: V_{GE}

Figure 8: Typical Output Characteristics



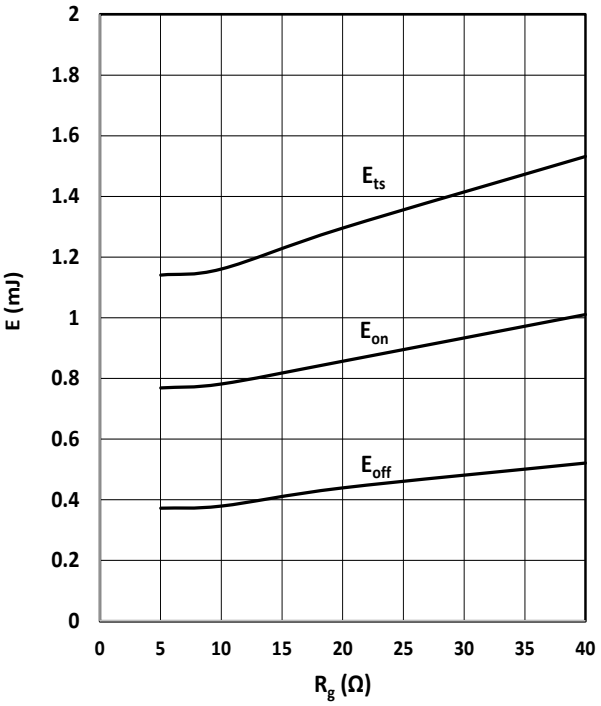
$I_C = f(V_{CE})$; Tj= 150ºC; parameter: V_{GE}

Figure 9: Typical switching energy losses as a function of collector current



E=f(Ic); V_{CE}=400V; Tj=25ºC; R_G=10Ω

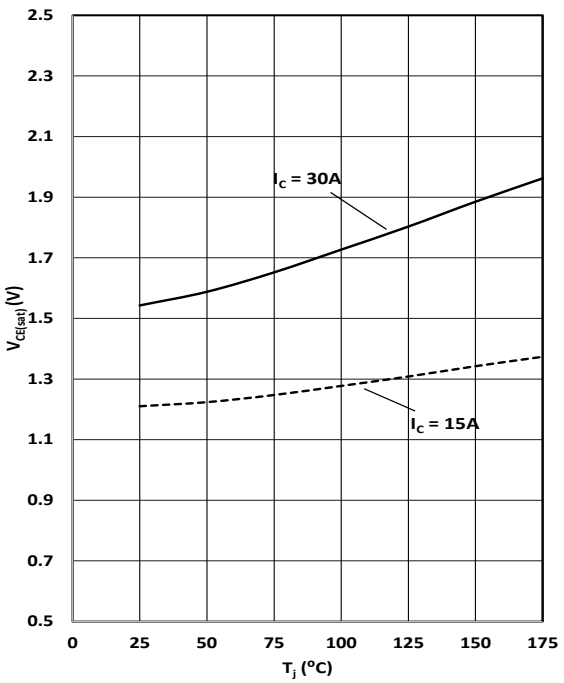
Figure10: Typical switching energy losses as a function of gate resistor



E=f(R_G); V_{CE}=400V; Tj=25ºC; Ic=30A

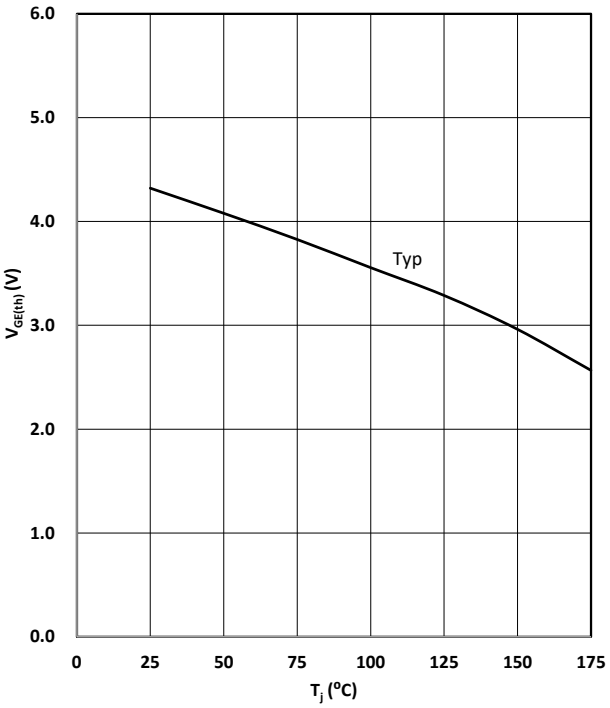
30A 650V Trench Field stop IGBT with anti-parallel diode SRE30N065FSU2DF

Figure 11: Typical collector-emitter saturation voltage as a function of junction temperature



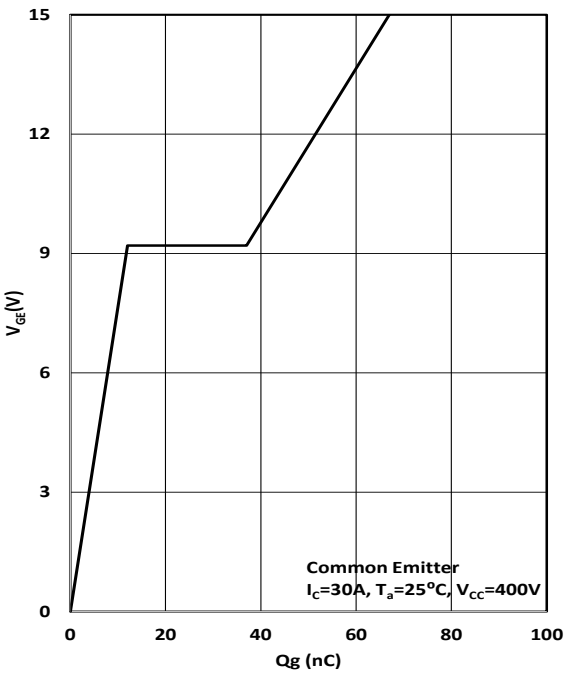
V_{CE} =f(T_j); V_{GE}=15V

Figure 12: Gate-emitter threshold voltage as a function of junction temperature



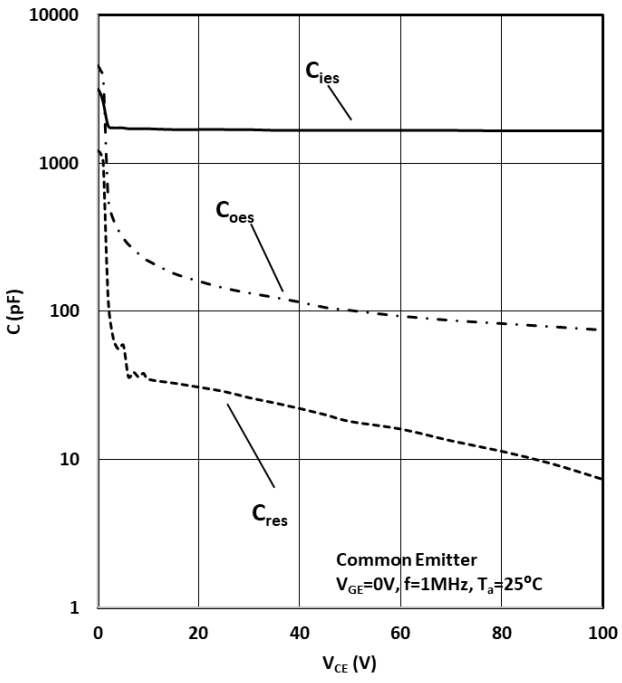
V_{GE} =f(T_j); I_{CE} = 250μA

Figure 13: Typical Gate Charge



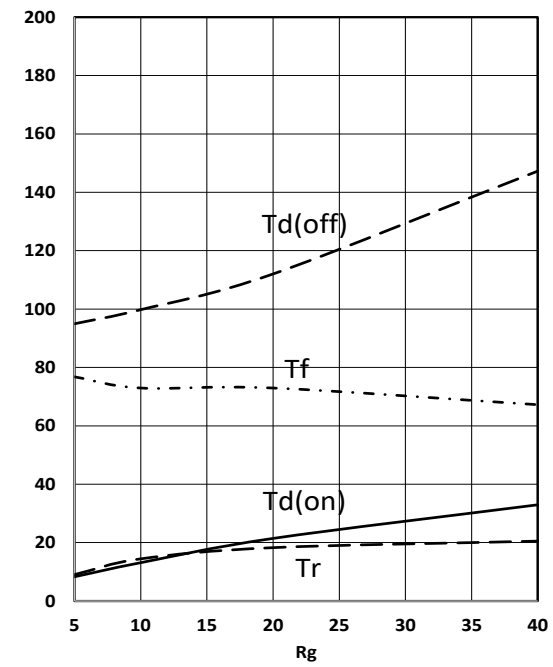
V_{GE}= f(Q_{gate}); I_C= 30A

Figure 14: Typical Capacitances



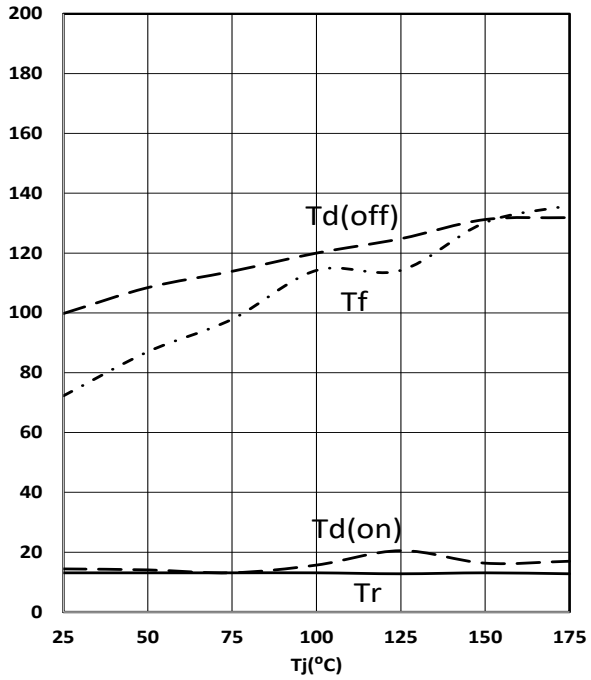
C=f(V_{CE}); V_{GE}=0; f=1MHz

Figure 15：Typical Switching time as a function of gate resistor



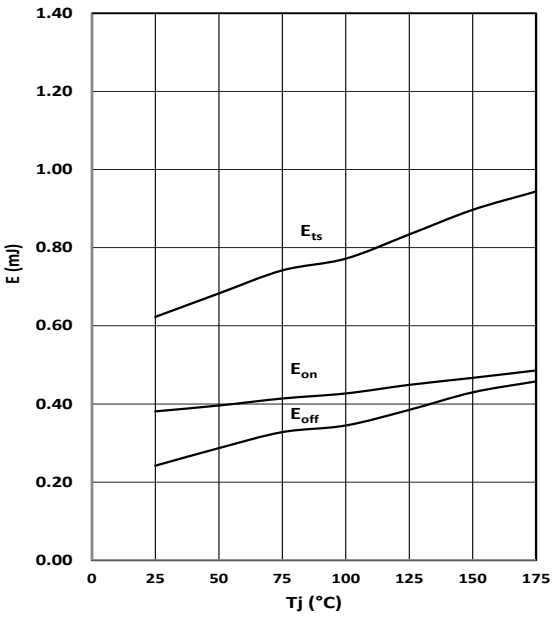
V_{CE}=400V;I_C=30A; Tj=25ºC

Figure 16: Typical Switching time as a function of junction temperature



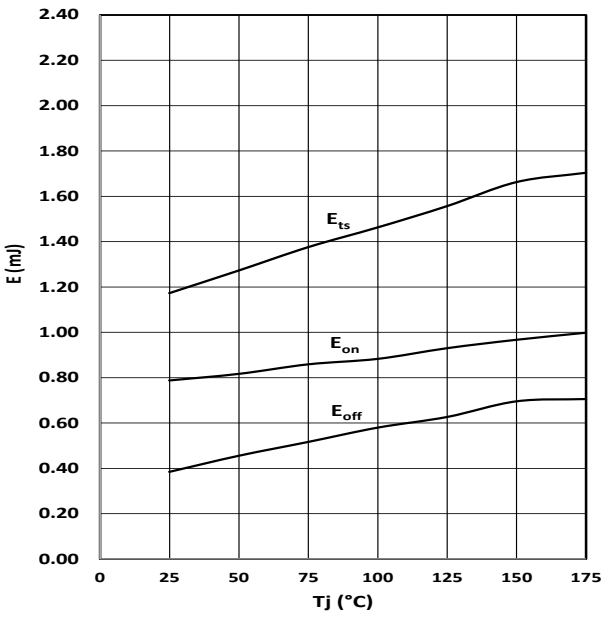
V_{CE} =400V; I_C = 30A;R_G=10Ω

Figure 17: Typical switching energy losses as a function of junction temperature

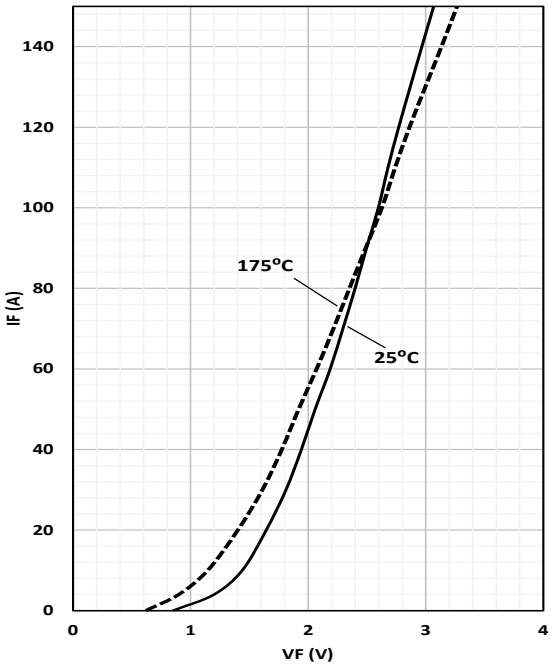
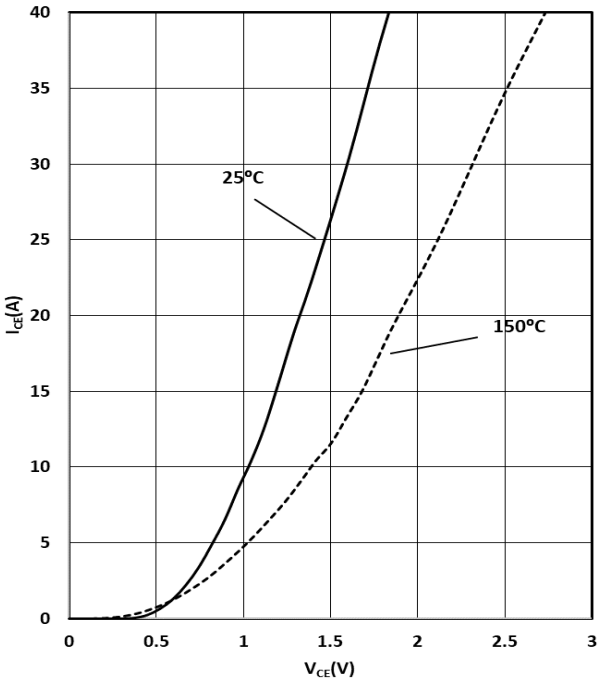


E= f(Tj); V_{CE}=400V;I_C=15A;R_G=10Ω

Figure 18: Typical switching energy losses as a function of junction temperature

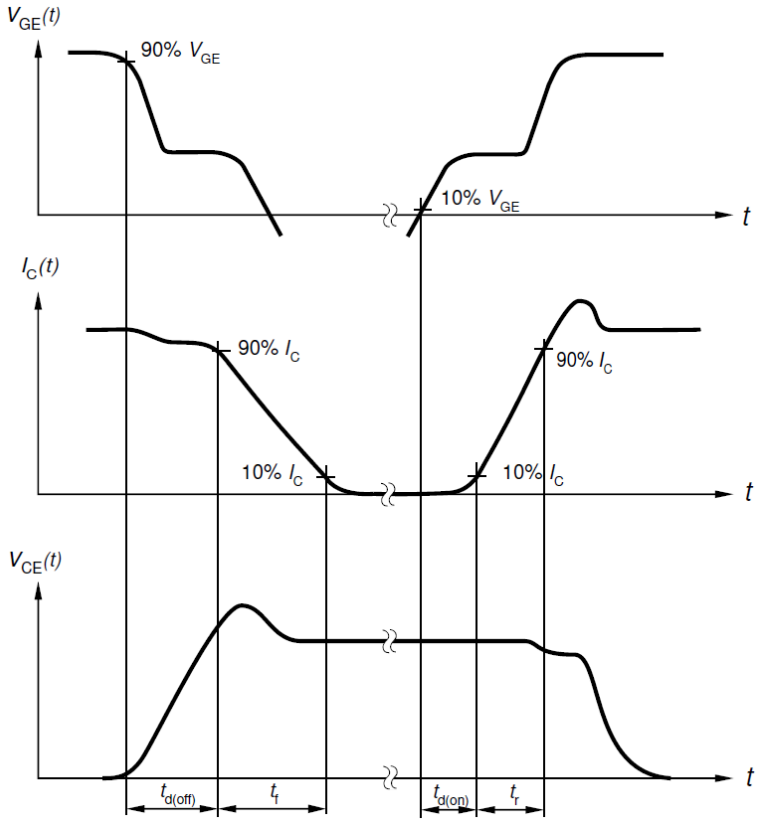


E= f(Tj); V_{CE}=400V;I_C=30A;R_G=10Ω

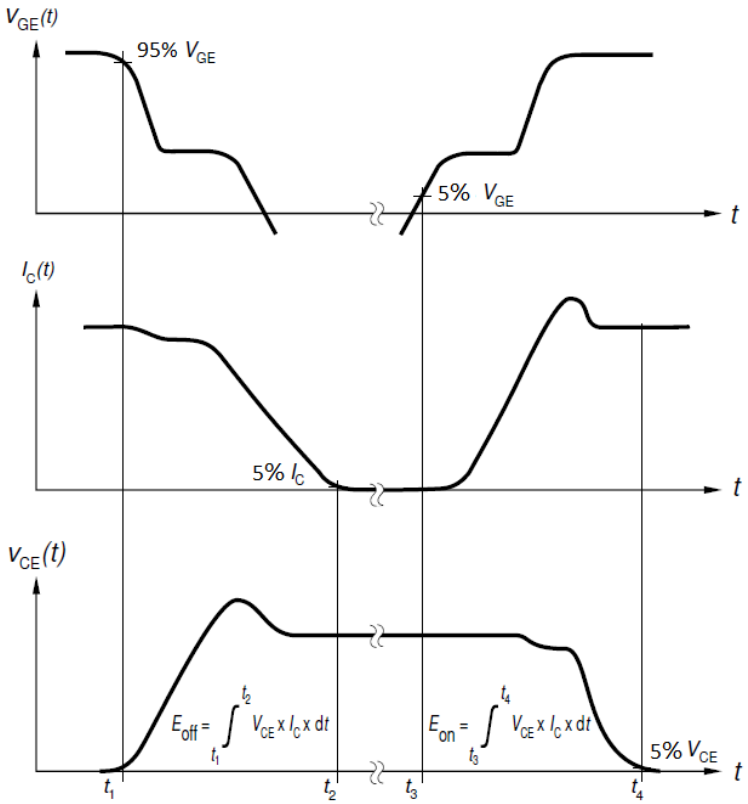
Figure 19: Typical diode forward current as a function of forward voltage	Figure 18: Typical transfer characteristic
	
IF= f(V_F);	I_C = f(V_{CE}); Tj= 25°C vs 150°C

Test Circuits

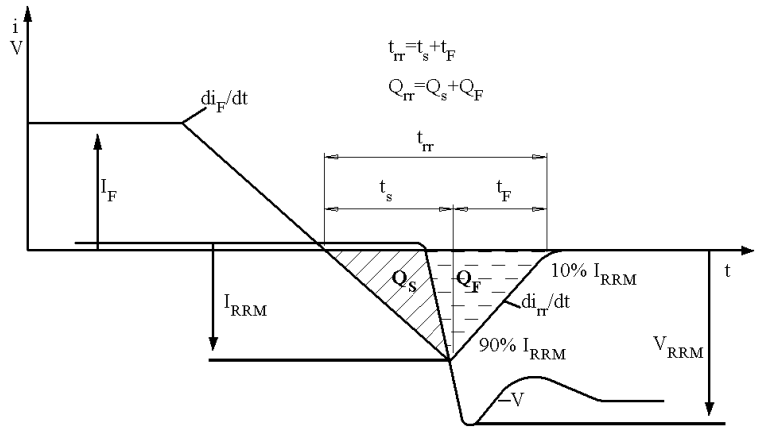
1. Definition Switching times



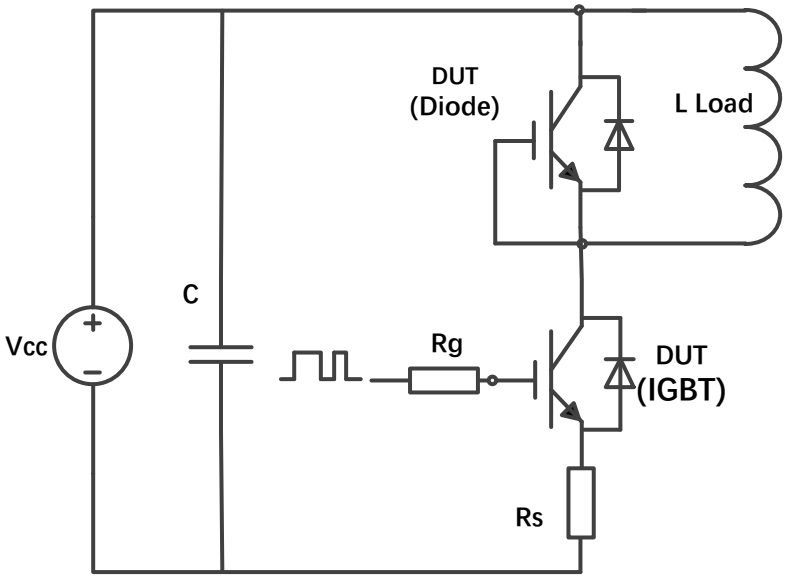
2. Definition Switching losses



3. Definition Diode Switching Characteristics



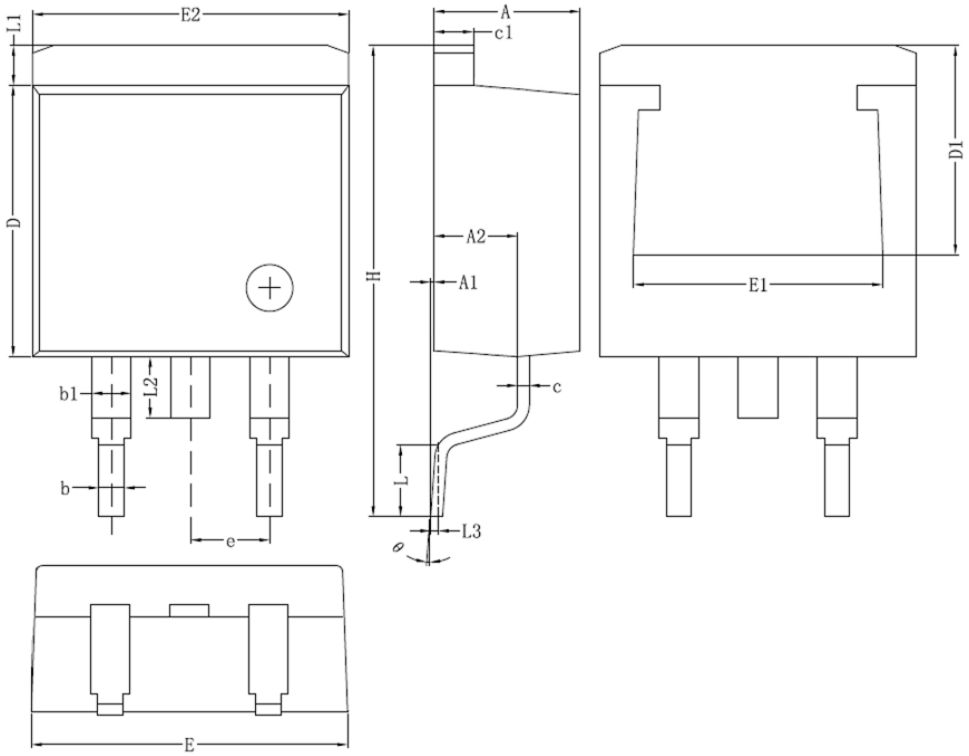
4. Dynamic test circuit



30A 650V Trench Field stop IGBT with anti-parallel diode SRE30N065FSU2DF

Mechanical Dimensions

TO-263 **Unit: mm**

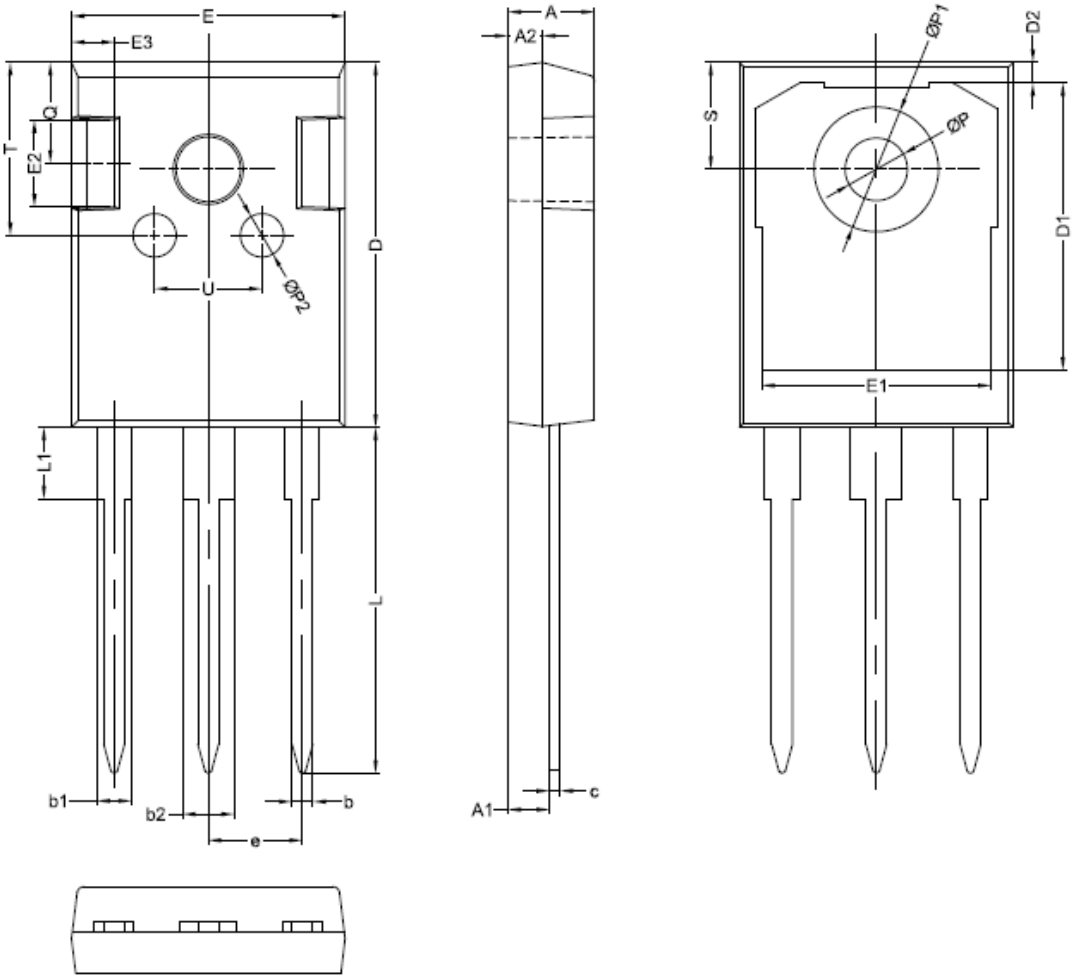


Symbol	Dimensions(mm)		
	Min.	Typ.	Max.
A	4.30	4.60	4.85
A1	0.00	0.10	0.25
A2	2.59	2.69	2.89
b	0.70	0.81	0.96
b1	-	1.27	-
c	0.36	0.40	0.61
c1	1.15	1.27	1.40
D	8.55	-	9.40
D1	6.40	-	-
E	9.80	10.10	10.31
E1	7.60	-	-
E2	9.80	10.00	10.20
e	2.54(BSC)		
H	14.70	15.20	16.00
L	2.00	2.30	2.84
L1	1.00	1.27	1.40
L2	-	-	2.20
L3	-	0.25	-
θ	0°	-	8°

30A 650V Trench Field stop IGBT with anti-parallel diode SRE30N065FSU2DF

TO-247

Unit: mm

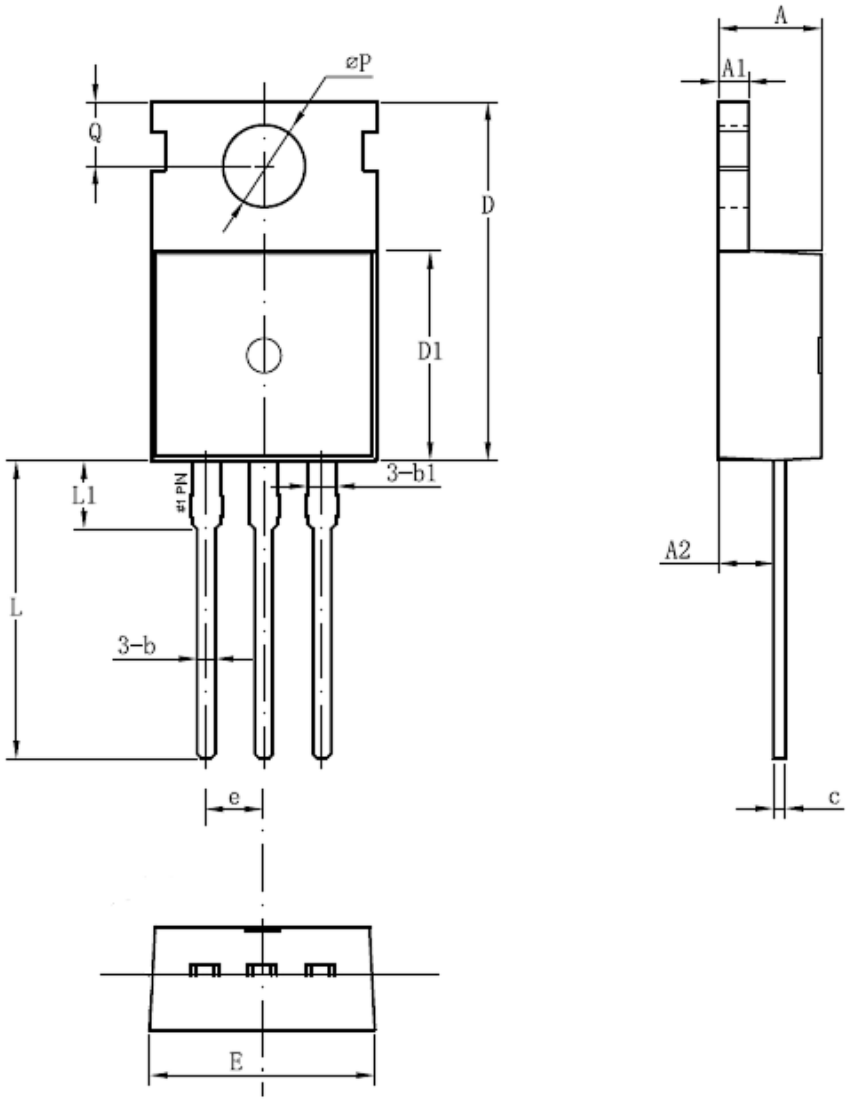


Symbol	Dimensions(mm)			Symbol	Dimensions(mm)		
	Min.	Typ.	Max.		Min.	Typ.	Max.
A	4.80	5.00	5.20	E2	-	5.00	-
A1	2.21	2.41	2.61	E3	-	2.50	-
A2	1.90	2.00	2.10	e	5.44(BSC)		
b	1.10	1.20	1.35	L	19.42	19.92	20.42
b1	-	2.00	-	L1	-	4.13	-
b2	-	3.00	-	P	3.50	3.60	3.70
c	0.55	0.60	0.75	P1	-	-	7.40
D	20.80	21.00	21.20	P2	-	2.50	-
D1	-	16.55	-	Q	-	5.80	-
D2	-	1.20	-	S	6.05	6.15	6.25
E	15.60	15.80	16.00	T	-	10.00	-
E1	-	13.30	-	U	-	6.20	-

30A 650V Trench Field stop IGBT with anti-parallel diode SRE30N065FSU2DF

TO-220C

Unit: mm



Symbol	Dimensions(mm)		
	Min.	Typ.	Max.
A	4.30	4.50	4.70
A1	1.20	1.30	1.40
A2	2.20	2.40	2.60
b	0.70	0.80	0.95
b1	-	1.27	-
c	0.40	0.50	0.65
D	15.20	15.70	16.20
D1	9.00	9.20	9.40
E	9.70	10.00	10.20
e	2.54(BSC)		
L	12.60	13.08	13.60
L1	-	3.00	-
ΦP	3.50	3.60	3.80
Q	2.60	2.80	3.00

30A 650V Trench Field stop IGBT with anti-parallel diode SRE30N065FSU2DF

Sanrise Technology Co., LTD

http://www.sanrise-tech.com

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